

#### Developmental\* Type ULNX-2103M†

## Baler

# SSFP (SHUNT-SERIES FEEDBACK PAIR) APR 1969

THE Type ULNX-2103M is a broadband amplifier fabricated within a monolithic silicon substrate. This device has a wide range of applications, in both industrial and commercial communication systems. Cascading the units with frequency-selective elements results in a wide range of i-f amplifiers.

This broadband amplifier offers the following design features:

- Frequency Response: 60 MHz at −3dB
- Voltage Gain: 31 dB typical
- 0 C to +85 C operating temperature range
- Optional emitter-follower input
- 8-lead plastic dual in-line "M" package.

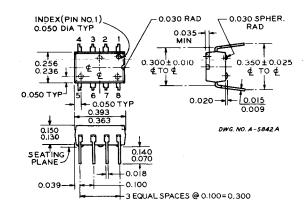
The Type ULNX-2103M broadband amplifier provides a current gain of 10 which is approximately  $\frac{Re+Rf}{Re}$ . The voltage gain is approximately  $\frac{RL}{Rs} \ x \ \frac{Rf}{Re}$  . The -3dB frequency point is defined by  $\frac{1}{RL CL}$ .

The basic amplifier is ideally suited to current amplification since the input impedance is about 10 ohms.

For some applications requiring a higher input impedance, it may be desirable to use the emitterfollower. This connection provides an input impedance of  $1.2K\Omega$  as defined by  $\frac{RB \times RS}{Rf}$ . When the emitter-follower input is used the f-3db point is not affected.

In some applications, the response may peak prior to f<sub>h</sub>, depending upon the values of R<sub>s</sub>, R<sub>l</sub> and C<sub>L</sub>. A capacitor, C<sub>f</sub>, may be connected in shunt with  $R_f$  (pins 4 and 8) to eliminate this peaking.

Variable-gain bandwidth characteristics can be obtained by paralleling the output-stage load re-



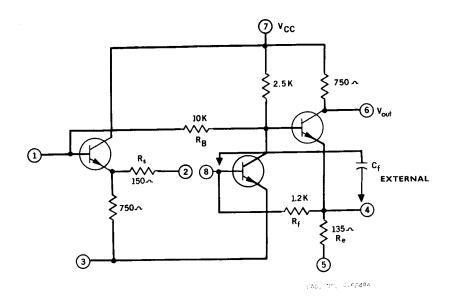
PACKAGE EM

#### **ABSOLUTE MAXIMUM RATINGS**

Power Supply+16V
Operating Temperature Range0 C to +85 C
Storage Temperature Range65 C to $+125$ C
Power Dissipation (internal)200mW

The SSFP Broadband Amplifler shown in this bulletin is presently fabricated in Sprague pilot plant facilities. When this device is transferred to regular production lines, the part number will be changed to ULN-2103M.

<sup>\*</sup>The right is reserved to withdraw this developmental integrated circuit from production at any time.



#### NOTES:

- 1. Use a series resistor  $\geq 100\Omega$  when pin 8 is used as the input.
- 2. Cf is an optional external capacitor. See text, page 1.
- 3. Pin 5 is connected internally to the substrate.

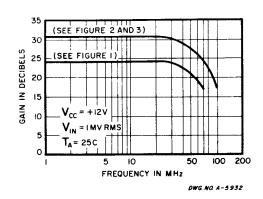
#### **ELECTRICAL CHARACTERISTICS**

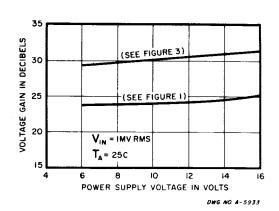
at  $V = +12 V_{DC}$ , T = 25 C, Pins 3 and 5 at Ground

Characteristics	Symbol	Test Conditions		Limits			
			Min.	Тур.	Max.	Units	Notes
Voltage Gain	A <sub>V</sub>	f = 1MHz, V <sub>in</sub> = 1mV@Pin 8, R <sub>L</sub> = 1KΩ	30	31	1	dB	1
Upper Frequency Cut-off	fh	$@$ -3dB point, $V_{out}$ $@$ Pin 6, $R_L = 1K\Omega$	50	60		MHz	1, 2
Output Voltage Swing	V <sub>o</sub>	f = 1MHz, Vout @ Pin 6, RL = 1KΩ			2.75	V <sub>rms</sub>	1
Power Supply Current	lycc			10		mA	
Output Quiescent Voltage	Vodc			6.7		V	
Input Resistance @ Pin 1	Rin			1.2K		Ω	
Input Resistance @ Pin 8	Rin			10		Ω	
Output Resistance	Rout	R <sub>out</sub> @ Pin 6		<i>7</i> 50		Ω	†

NOTES: 1. Use a  $100\Omega$  series resistor to apply input signal to Pin 8.

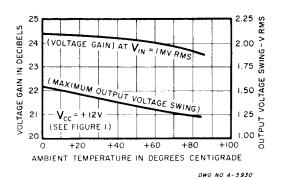
2. Use 2.5pF probe (Boonton 91-12E, or equivalent).

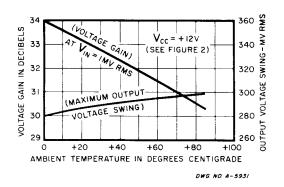




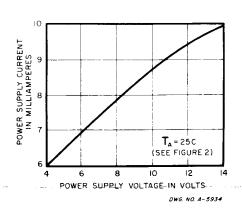
AMPLIFIER VOLTAGE GAIN AS A FUNCTION OF FREQUENCY

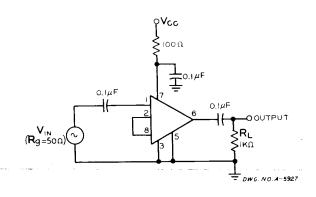
VOLTAGE GAIN AS A FUNCTION OF POWER SUPPLY VOLTAGE





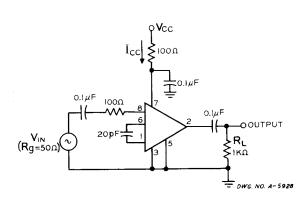
### VOLTAGE GAIN AND OUTPUT VOLTAGE SWING AS A FUNCTION OF AMBIENT TEMPERATURE





POWER SUPPLY CURRENT AS A FUNCTION OF POWER SUPPLY VOLTAGE

FIGURE 1



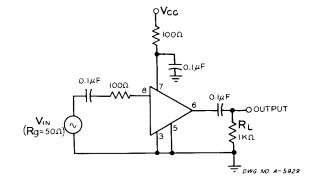


FIGURE 2

FIGURE 3

